

3V Quad-Band GSM850/GSM900/DCS/PCS Power Amplifier Module

Absolute Maximum Ratings

Symbol	Parameter	Absolute Maximum Value	Units
V _{BATT}	Positive Supply Voltage	-0.5 to +5.5	VDC
V _{RAMP}	Power Control Voltage	-0.3 to +2.5	VDC
δ	Duty Cycle at Maximum Power	50	%
T _{STG}	Storage Temperature	-55 to +150	°C
T _C	Operating Case Temperature	-25 to +90	°C
P _I	Maximum Input Power	+13	dBm

Note: The part may not survive all maximums applied simultaneously.

Mode 1 Electrical Characteristics¹

Parameter	Conditions	Min.	Typ/Nom	Max.	Units
Supply Voltage, V _{BATT}		3.0	3.5	4.8	V _{dc}
Transmit Enable, TX_EN Voltage	Logic High	1.25		3	V
	Logic Low	-0.2		0.4	V
Transmit Enable, TX_EN Current	Logic High			10	μA
	Logic Low			10	μA
Band Select Voltage	Logic High: DCS	1.25		3	V
	Logic Low: GSM	-0.2		0.4	V
Band Select Current- DCS/GSM	High/Low			10	μA
Leakage Current TX_EN Low	V _{ramp} = 0.2V; T = -25°C, +85°C		5	15	μA
Input and Output Load Impedance			50		Ω
V _{ramp} MIN			0	0.25	V
V _{ramp}		0		1.45	V
V _{ramp} Input Current	V _{ramp} = 0.2V, 1.45V			10	μA
Operating Case Temperature		-25		+90	°C

Note 1: Test Conditions: BS = L, V_{BATT} = 3.5V, V_{RAMP} = 1.45V, P_{IN} = 6 dBm, TX_EN = H, T_C = 25°C, Duty Cycle = 25% unless otherwise specified.

Data Sheet

For additional information and latest specifications, see our website: www.triquint.com

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